

NPN HIGH SPEED SATURATED SWITCHES

2N930

NPN LOW LEVEL LOW NOISE AMPLIFIER DIFFUSED SILICON PLANAR* EPITAXIAL TRANSISTOR

- $V_{CEO} \dots 45 \text{ V (MIN)}$
- $h_{FE} \dots 100\text{--}300 @ 10 \mu\text{A}$
- $NF \dots 3.0 \text{ dB (MAX) @ } 1.0 \text{ kHz}$

ABSOLUTE MAXIMUM RATINGS (Note 1)

Maximum Temperatures

Storage Temperature

Operating Junction Temperature

Lead Temperature (10 seconds)

-65°C to $+200^{\circ}\text{C}$

175°C

300°C

Maximum Power Dissipation (Notes 2 & 3)

Total Dissipation at 25°C Case Temperature

at 25°C Ambient Temperature

0.6 W

0.3 W

Maximum Voltages and Current

V_{CBO} Collector to Base Voltage

V_{CEO} Collector to Emitter Voltage (Note 4)

V_{EBO} Emitter to Base Voltage

I_C Collector Current

45 V

45 V

5.0 V

30 mA

See TO18.



ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN.	MAX.	UNITS	TEST CONDITIONS
h_{FE}	DC Pulse Current Gain (Note 5)		600		$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$
h_{FE}	DC Current Gain	150			$I_C = 500 \mu\text{A}, V_{CE} = 5.0 \text{ V}$
		100	300		$I_C = 10 \mu\text{A}, V_{CE} = 5.0 \text{ V}$
		20			$I_C = 10 \mu\text{A}, V_{CE} = 5.0 \text{ V}, T_A = -55^{\circ}\text{C}$
$V_{BE(sat)}$	Base to Emitter Saturation Voltage (Note 5)	0.6	1.0	V	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$
$V_{CE(sat)}$	Collector Saturation Voltage (Note 5)		1.0	V	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$
h_{ib}	Input Resistance	25	32	Ω	$I_C = 1.0 \text{ mA}, V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$
h_{ob}	Output Conductance		1.0	μmho	$I_C = 1.0 \text{ mA}, V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$
h_{rb}	Voltage Feedback Ratio		600	$\times 10^{-6}$	$I_C = 1.0 \text{ mA}, V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$
h_{fe}	Small Signal Current Gain	150	600		$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$
h_{fe}	High Frequency Current Gain	1.0			$I_C = 500 \mu\text{A}, V_{CE} = 5.0 \text{ V}, f = 30 \text{ MHz}$
I_{CBO}	Collector to Base Cutoff Current		10	nA	$I_E = 0, V_{CB} = 45 \text{ V}$
I_{CES}	Collector to Emitter Cutoff Current		10	nA	$V_{CE} = 45 \text{ V}, V_{EB} = 0$
			10	μA	$V_{CE} = 45 \text{ V}, V_{EB} = 0, T_A = 170^{\circ}\text{C}$
I_{EBO}	Emitter to Base Cutoff Current		10	nA	$I_C = 0, V_{EB} = 5.0 \text{ V}$
I_{CEO}	Collector to Emitter Cutoff Current		2.0	nA	$I_B = 0, V_{CE} = 5.0 \text{ V}$
c_{ob}	Output Capacitance		8.0	pF	$I_E = 0, V_{CB} = 5.0 \text{ V}$
n	Noise Figure		3.0	dB	$I_C = 10 \mu\text{A}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}, R_S = 10 \text{ k}\Omega, BW = 15.7 \text{ kHz}$
$E_O(sus)$	Collector to Emitter Sustaining Voltage (Notes 4 & 5)	45		V	$I_C = 10 \text{ mA}, I_B = 0 \text{ (pulsed)}$
B_O	Emitter to Base Breakdown Voltage	5.0		V	$I_C = 0, I_E = 10 \text{ nA}$

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.